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--CROSS REFERENCE TO RELATED APPLICATIONS

Applicants claim priority under 35 U.S.C. §119 of German Patent Application Serial No. 199 09 557.4, filed on March 4, 1999 and German Patent Application Serial No. 100 04 623.1 filed February 3, 2000. Applicants also claim priority under 35 U.S.C. §120 of International Application PCT/EP00/01800, filed on March 2, 2000. The International Application under PCT article 21(2) was not published in English.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The invention relates to a semiconductor wafer with a thin epitaxial layer, and a process for producing the semiconductor wafer by depositing the layer on a substrate wafer made of monocrystalline silicon.--

On page 1 between the first paragraph and the second paragraph, please insert the following paragraphs:

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-- 2. The Prior Art

EP-829559 A1 discloses a process for producing semiconductor wafers with a low defect density, it being necessary to provide a single crystal which has to be pulled with forced cooling or has to have a specific oxygen and nitrogen

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concentration, and semiconductor wafers obtained from the single crystal having to be subjected to heat treatment. EP-644588 A1 relates to a semiconductor wafer having an epitaxially provided layer which has a low defect density and originates from a single crystal pulled at a pulling rate of at more 0.6 mm/min.--

On page 2, between the top paragraph and the first complete paragraph on this page, please insert:

--SUMMARY OF THE INVENTION--

On Page 2, please cancel the second complete paragraph on this page, and please rewrite by replacing with the following paragraph:

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--The invention relates to a semiconductor wafer comprising a substrate wafer made of monocrystalline silicon and an epitaxial layer deposited thereon, which is characterized in that the substrate wafer has a resistivity of from 0.1 to 50 Ωcm , an oxygen concentration of less than $7.5 \times 10^{17} \text{ atcm}^{-3}$, and a nitrogen concentration of from 1×10^{-13} to $5 \times 10^{15} \text{ atcm}^{-3}$, and the epitaxial layer has a thickness of from 0.2 to 1.0 μm and has a surface on which fewer than 30 LLS defects with a size of more than 0.085 μm can be detected.--

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On page 6, in the line above the word "Example", please insert: